ΡΛΝ	JIT
	SEMI
	CONDUCTOR

100V N-Channel Enhancement Mode MOSFET

Current 42A

Features

Voltage

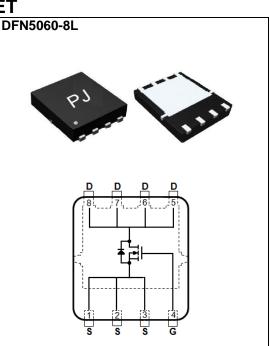
- RDS(ON), VGS@10V, ID@20A<25mΩ
- RDS(ON), VGS@4.5V, ID@15A<28.5mΩ

100 V

- Advanced Trench Process Technology
- · High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case: DFN5060-8L Package
- Terminals: Solderable per MIL-STD-750, Method 2026 ٠
- Approx. Weight: 0.0028 ounces, 0.08 grams
- Marking: Q5476AL •



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAME	TER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V _{DS}	100	V
Gate-Source Voltage		V _{GS}	<u>+</u> 20	V
Continuous Drain Current	Tc=25°C		42	
	T _C =100°C	I _D	26.6	А
Pulsed Drain Current (Note 1)	Tc=25°C	I _{DM}	150	
Power Dissipation	T _C =25°C	_	83	
	Tc=100°C	PD	33	W
	T _A =25°C	6.5	А	
Continuous Drain Current	T _A =70°C	ID	5.2	А
Power Dissipation	T _A =25°C	_	2.0	
	T _A =70°C	PD	1.3	W
Single Pulse Avalanche Energ	y ^(Note 6)	E _{AS}	63.4	mJ
Operating Junction and Storag	e Temperature Range	TJ,TSTG	-55~150	٥C
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	R _{θJC}	1.5	
	Junction to Ambient	R _{θJA}	62.5	°C/W

Maximum Junction Temperature nited only By



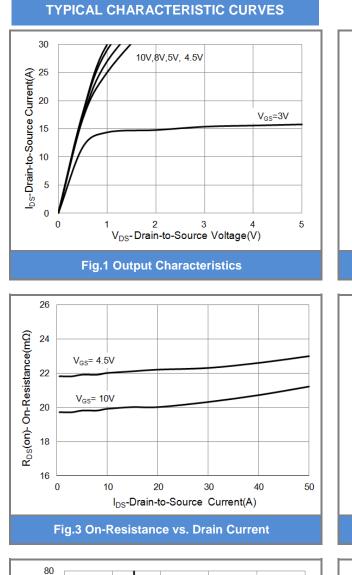
Electrical Characteristics (T_A=25°C unless otherwise noted)

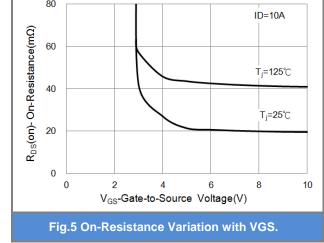
				T \/D			
PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static	1	1	1	T	T	T	
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA	100	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1.0	1.8	2.5	V	
	_	V _{GS} =10V,I _D =20A	-	20	25		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =4.5V,I _D =15A	-	22	28.5	mΩ	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =80V,V _{GS} =0V	-	-	1.0	uA	
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA	
Dynamic (Note 7)		·					
Total Gate Charge	Qg	V _{DS} =50V, I _D =10A,	-	31	-	nC	
Gate-Source Charge	Qgs		-	5.1	-		
Gate-Drain Charge	Qgd	V _{GS} =10V (Note 1,2)	-	7.3	-		
Input Capacitance	Ciss		-	1519	-	pF	
Output Capacitance	Coss	$V_{DS}=30V, V_{GS}=0V,$	-	132	-		
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	66	-		
Turn-On Delay Time	td(on)		-	11	-		
Turn-On Rise Time	tr	V _{DD} =50V, I _D =10A,	-	42	-		
Turn-Off Delay Time	td(off)	V _{GS} =10V,	-	40	-	ns	
Turn-Off Fall Time	tf	R _G =3Ω ^(Note 1,2)	-	19	-		
Drain-Source Diode			•				
Maximum Continuous Drain-Source					10	•	
Diode Forward Current	I _S		-	-	42	A	
Diode Forward Voltage	V _{SD}	I _S =1A,V _{GS} =0V	-	0.7	1.2	V	

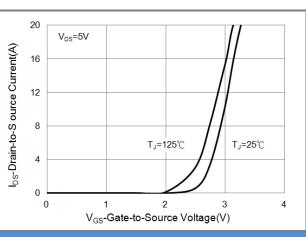
NOTES :

- 1. Pulse width
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited.
- 5. $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=3mH, I_{AS} =6.5A, V_{DD} =50V, V_{GS} =10V
- 7. Guaranteed by design, not subject to production testing.











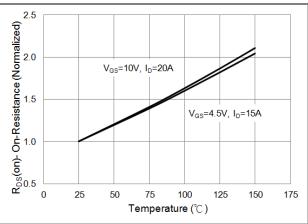
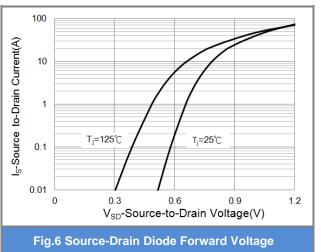


Fig.4 On-Resistance vs. Junction temperature





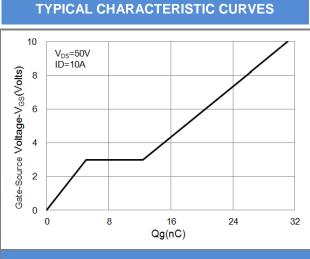


Fig.7 Gate-Charge Characteristics

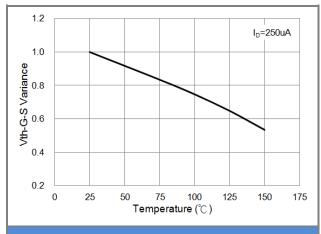
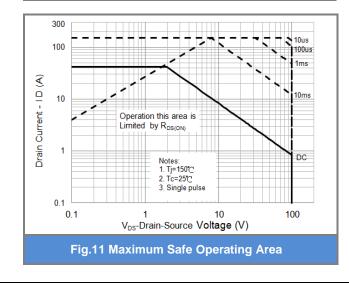
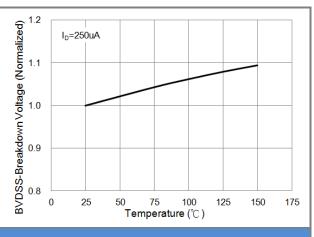


Fig.9 Threshold Voltage Variation with Temperature







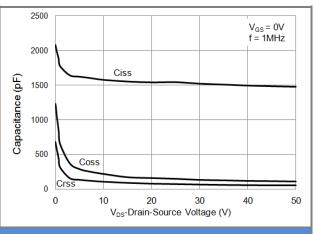
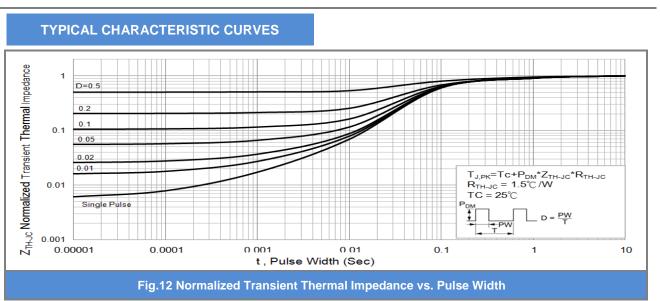


Fig.10 Capacitance vs. Drain-Source Voltage



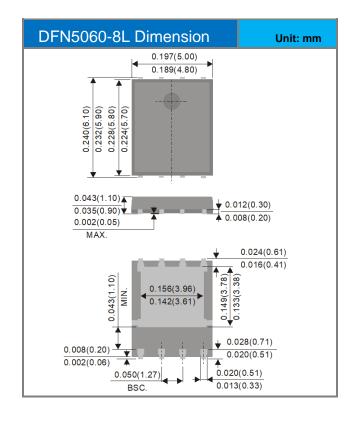


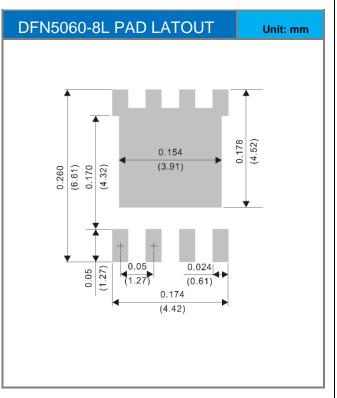


Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJQ5476AL	DFN5060-8L	3000pcs / 13" reel	Q5476AL

Packaging Information & Mounting Pad Layout







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